

**Amendments to the Specification**

Please change paragraph [0025] as follows:

Dielectric 36 comprises an insulative polish stop layer 44 received over (and preferably "on", as shown) insulative material 38. Such will provide an effective ~~polished~~ polish stopping function, as will be apparent subsequently, relative to polishing of materials lying thereover. By way of example only and in preferred embodiments, exemplary materials for layer 44 include undoped SiO<sub>2</sub>, silicon nitride, or a combination thereof. In one preferred embodiment, layer 44 consists essentially of silicon nitride. Further by way of example only, additional materials for layer 44 include insulative metal oxides, for example at least one of tantalum oxide, aluminum oxide and hafnium oxide, including mixtures thereof. Further in one preferred embodiment, and by way of example only, insulative polish stop layer 44 has a thickness from about 500 Angstroms to about 2,000 Angstroms, and in one preferred embodiment is substantially homogeneous. In one preferred embodiment, insulative polish stop layer 44 comprises undoped SiO<sub>2</sub>, and at least outermost portion of insulative material 38 comprises doped SiO<sub>2</sub>.

Please change paragraph [0028] as follows:

Referring to Figs. 4 and 5, at least a portion of contact opening 50 is widened into a contact opening 51 with an etching chemistry that is selective to widen contact opening 50 within insulative material 38 to a degree greater than any widening which occurs to ~~contacting~~ contact opening 50 within insulative polish stop layer 44. For purposes of illustration and by way of example only, Fig. 4 depicts the exemplary respective outlines of original contact opening 50 and what will be widened contact opening 51. In the depicted preferred embodiment, the widening is also depicted as widening contact opening 50 within insulator layer 46. In one preferred embodiment, the widening is selective to widen the contact opening within the insulative material to a degree that is at least two times greater than any widening of the contact opening within the insulative polish stop layer, and more preferably much greater than this, for example at least fifty times greater than any widening of the contact opening within the insulative polish stop layer. Where, for example, materials 46 and 42 comprise doped  $\text{SiO}_2$ , and material 44 comprises silicon nitride or undoped  $\text{SiO}_2$ , an exemplary etching chemistry is an aqueous liquid such as dilute HF, a combination of ammonium

fluoride and phosphoric acid, or a combination of isopropyl alcohol, ammonium fluoride and dilute HF. Etching with such can be by either spray or bath dip at an exemplary temperature of 20°C to 40°C for from about 1 minute to 45 minutes to produce the illustrated effect, as well as clear any native oxide or other material from over node location 34. Selectivity of doped oxide to undoped oxide in such instance is typically from about 2:1 to 5:1, while that for doped oxide to  $\text{Si}_3\text{N}_4$  is about 200:1.